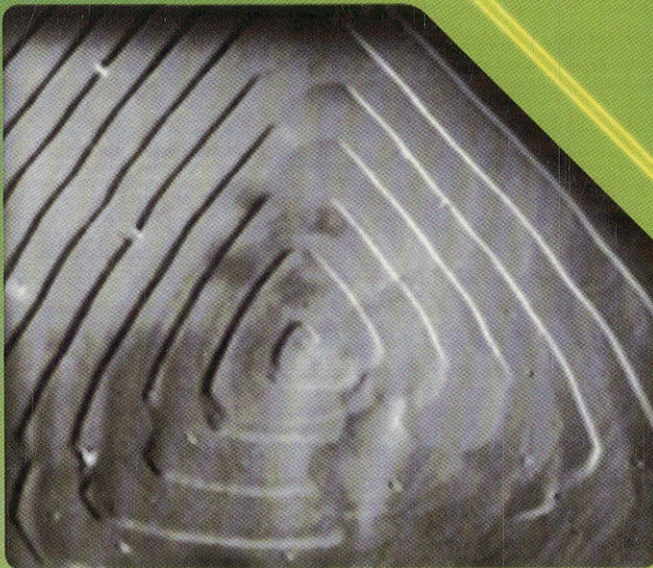


Edited by  
**Peter Capper**

# Bulk Crystal Growth

of Electronic, Optical  
and Optoelectronic  
Materials



 **WILEY**

Wiley Series  
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Applications



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